Transistor IGBT, G80N60UFD, 600 V, 80 A

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The G80N60UFD is an ultrafast 600 V, 80 A insulated-gate bipolar transistor in a robust TO-3P package, designed for high-efficiency industrial inverters. Combining MOSFET-like gate control with low saturation voltage and a co-pack fast recovery diode, it is ideal for motor drives, induction heating, welding machines, UPS and PFC stages.